

HZM6.2ZFA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-593(Z)

Rev 0

Nov. 1997

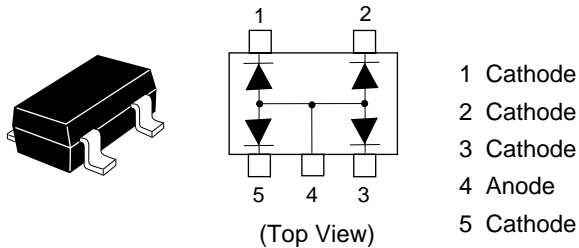
Features

- HZM6.2ZFA has four devices, and can absorb external + and -surge.
- Low capacitance ($C=8.5\text{pF}$ max) and can protect ESD of signal line.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.2ZFA	62Z	MPAK-5

Outline



HZM6.2ZFA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd ^{*1}	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, See Fig.2.

Electrical Characteristics (Ta = 25°C)^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _Z	5.90	—	6.50	V	I _Z = 5 mA, 40ms pulse
Reverse current	I _R	—	—	3	μA	V _R = 5.5V
Capacitance	C	—	8.0	8.5	pF	V _R = 0V, f = 1 MHz
Dynamic resistance	r _d	—	—	60	Ω	I _Z = 5 mA
ESD-Capability ^{*2}	—	13	—	—	kV	C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes 1. Per one device.

2. Failure criterion ; IR > 3 μA at VR = 5.5V.

Main Characteristic

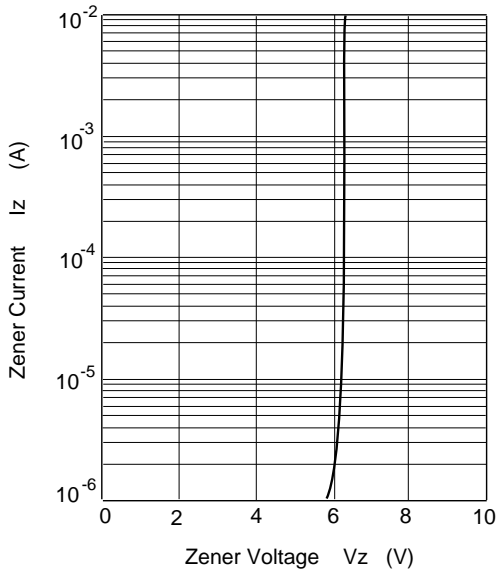


Fig.1 Zener current Vs. Zener voltage

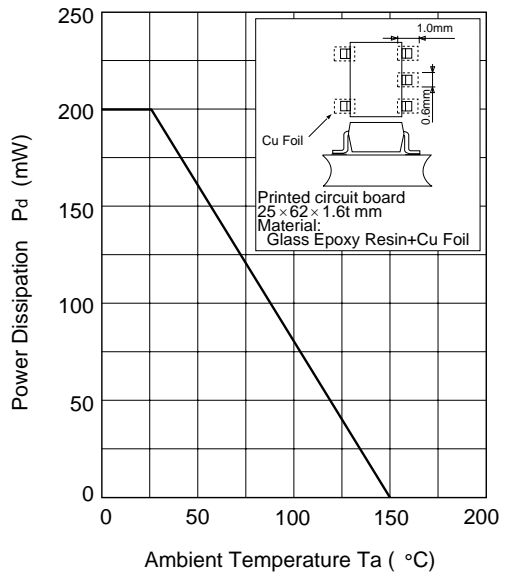


Fig.2 Power Dissipation Vs. Ambient Temperature

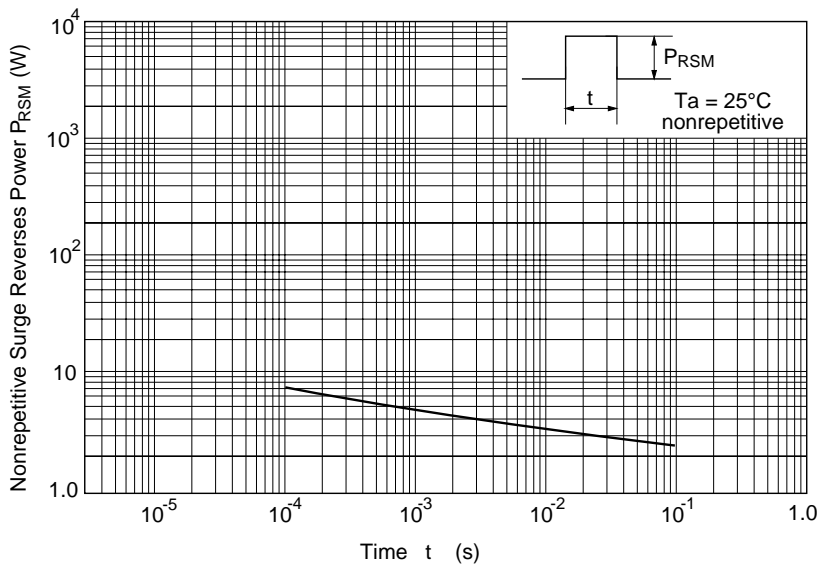


Fig.3 Surge Reverse Power Ratings

Main Characteristic

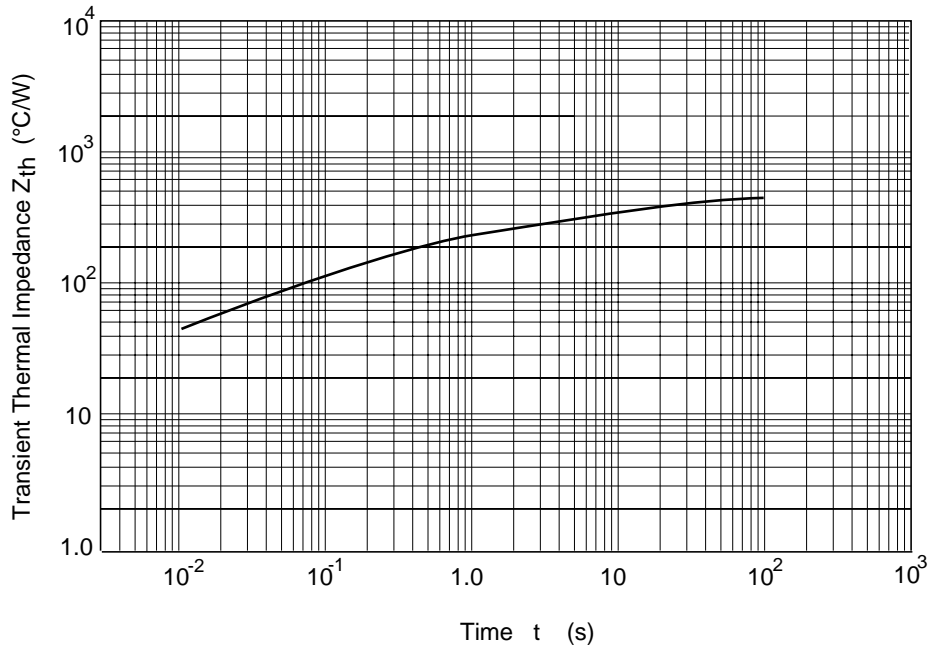
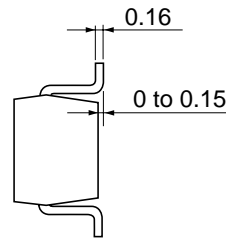
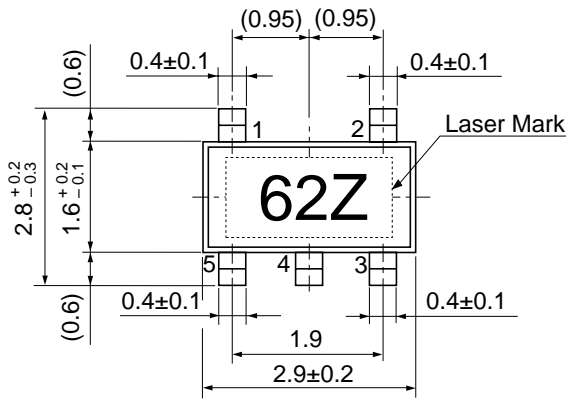


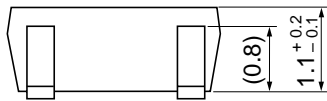
Fig.4 Transient Thermal Impedance

Package Dimensions

Unit : mm



- 1 Cathode
- 2 Cathode
- 3 Cathode
- 4 Anode
- 5 Cathode



Hitachi Code	MPAK-5
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.013

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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